

## Schottky Power Diode, 80A

**Features**

- Fast Switching
- Low forward voltage drop
- High surge capability
- High efficiency, low power loss
- Normal and Reverse polarity



DO-203AB (DO-5)

**Maximum Ratings** ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)

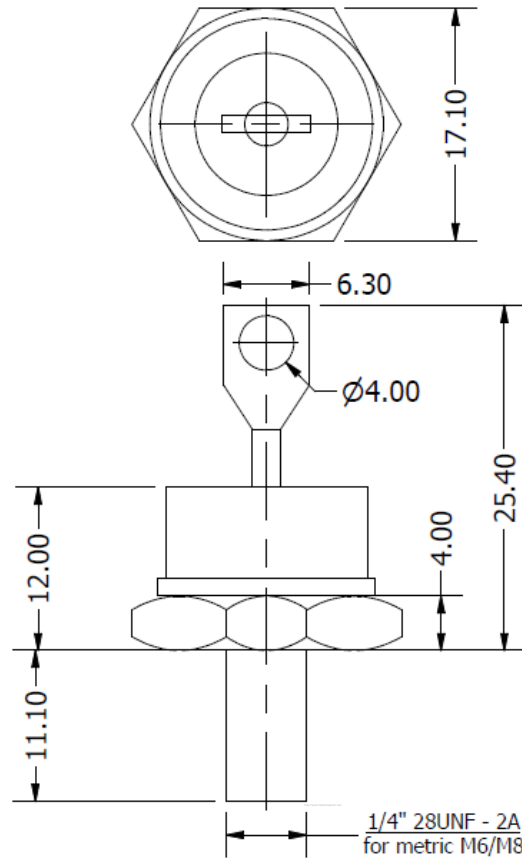
Parameter	Test Conditions	Symbol	MBR8045(R)	MBR8060(R)	MBR8080(R)	MBR80100(R)	Unit
Repetitive peak reverse voltage		$V_{RRM}$	45	60	80	100	V
RMS reverse voltage		$V_{RMS}$	32	42	57	70	V
DC blocking voltage		$V_{DC}$	45	60	80	100	V
Continuous forward current	$T_C \leq 120^\circ\text{C}$	$I_F$	80	80	80	80	A
Surge non-repetitive forward current, half-sine wave	$T_C = 25^\circ\text{C}$	$I_{FSM}$	1000	1000	1000	1000	A
Forward voltage	$I_F = 80\text{ A}$ $T_J = 25^\circ\text{C}$	$V_F$	0.65	0.75	0.84	0.84	V
Reverse current	$V_R = 20\text{ V}$ , $T_J = 25^\circ\text{C}$	$I_R$	5	5	5	5	mA
	$V_R = 20\text{ V}$ , $T_J = 125^\circ\text{C}$		250	250	250	250	

**Thermal & Mechanical Specifications** ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)

Parameters	Symbol	MBR8045(R)	MBR8060(R)	MBR8080(R)	MBR80100(R)	Unit
Maximum thermal resistance, junction to case	$R_{th(jc)}$	1.0				$^\circ\text{C/W}$
Operating junction temperature range	$T_J$	-65 to 150				$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 to 175				$^\circ\text{C}$
Mounting torque (non-lubricated threads)	F	4.0				Nm
Approximate allowable weight	W	17.0				g



Package Outline



ALL DIMENSIONS IN MM